Salim Berrada

List of Publications by Year
in descending order

15 papers	141 citations	1307594 7 h-index	1588992 8 g-index
15 all docs	15 docs citations	15 times ranked	97 citing authors

#	Article	IF	Citations
1	Nano-electronic Simulation Software (NESS): a flexible nano-device simulation platform. Journal of Computational Electronics, 2020, 19, 1031-1046.	2.5	20
2	Surface Roughness Scattering in NEGF using self-energy formulation. , 2019, , .		3
3	Investigation of Pt-Salt-Doped-Standalone- Multiwall Carbon Nanotubes for On-Chip Interconnect Applications. IEEE Transactions on Electron Devices, 2019, 66, 2346-2352.	3.0	13
4	Simulation of the Impact of Ionized Impurity Scattering on the Total Mobility in Si Nanowire Transistors. Materials, 2019, 12, 124.	2.9	21
5	Comprehensive Study of Cross-Section Dependent Effective Masses for Silicon Based Gate-All-Around Transistors. Applied Sciences (Switzerland), 2019, 9, 1895.	2.5	15
6	Atomistic- to Circuit-Level Modeling of Doped SWCNT for On-Chip Interconnects. IEEE Nanotechnology Magazine, 2018, 17, 1084-1088.	2.0	7
7	Efficient Two-Band based Non-Equilibrium Green's Function Scheme for Modeling Tunneling Nano-Devices. , 2018, , .		4
8	Variability Predictions for the Next Technology Generations of n-type SixGe1â^'x Nanowire MOSFETs. Micromachines, 2018, 9, 643.	2.9	7
9	Nanowire FETs. , 2018, , .		0
10	The Impact of Dopant Diffusion on Random Dopant Fluctuation in Si Nanowire FETs: A Quantum Transport Study. , 2018, , .		3
11	NESS: new flexible Nano-Electronic Simulation Software. , 2018, , .		20
12	Impact of the Effective Mass on the Mobility in Si Nanowire Transistors. , 2018, , .		4
13	Quantum Transport Investigation of Threshold Voltage Variability in Sub-10 nm JunctionlessSi Nanowire FETs. , 2018, , .		3
14	Random Dopant-Induced Variability in Si-InAs Nanowire Tunnel FETs: A Quantum Transport Simulation Study. IEEE Electron Device Letters, 2018, 39, 1473-1476.	3.9	11
15	Understanding Electromigration in Cu-CNT Composite Interconnects: A Multiscale Electrothermal Simulation Study. IEEE Transactions on Electron Devices, 2018, 65, 3884-3892.	3.0	10